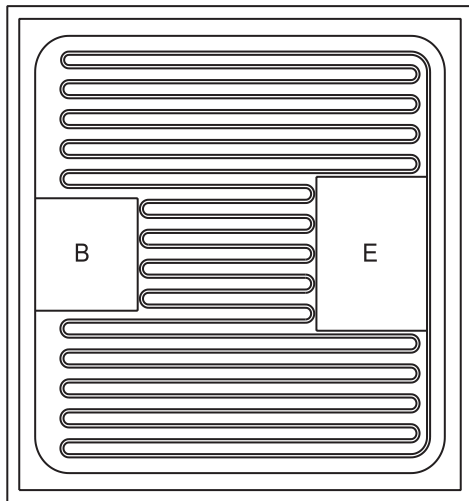


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	41.3 x 41.3 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	9.5 x 9.2 MILS
Emitter Bonding Pad Area	12.8 x 10.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**

6,670

**PRINCIPAL DEVICE TYPES**

- CMPT3090L
- CXT3090L
- CZT3090L
- CMXT3090L

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
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R1 (1-August 2002)

The Typical Electrical Characteristics data  
for this chip is currently being revised.

For the latest updated data for this Chip Process,  
please visit our website at:

[www.centrasemi.com/chip](http://www.centrasemi.com/chip)

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